
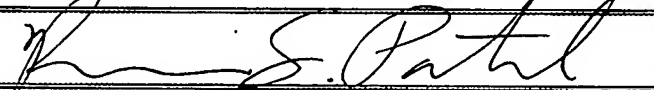


FORM PTO-1449 (Rev. 2-32)	U.S. Department of Commerce Patent and Trademark Office	Atty. Docket No.	Serial No.
		05-720-US2	10/559,981
		Applicant: Kouvetakis, et al.	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		Filing Date:	Group:
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U.S. PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
RSP	1.	US 2003-0157787 A1	August 21, 2003	Murthy, et al.	—	—	
	2.	US 2006-0134895 A1	June 22, 2006	Kouvetakis, et al.	—	—	
	3.	US 2006-0236923 A1	October 26, 2006	Kouvetakis, et al.	—	—	
	4.	US 2006-0163612-A1	July 27, 2006	Kouvetakis, et al.	—	—	
	5.	6,911,084	June 28, 2005	Kouvetakis, et al.	—	—	
	6.	5,532,183	July 2, 1996	Sugawara, et al.	—	—	
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	9.	6,410,434	June 25, 2002	Mani	—	—	
	10.	6,723,621	April 20, 2004	Cordone, et al.	—	—	
	11.	6,897,471	May 24, 2005	Soref, et al.	—	—	
	12.	6,441,716	August 27, 2002	Doppalapudi, et al.	—	—	

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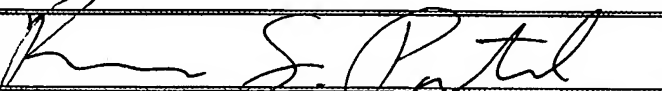
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Examiner Initial		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
RSP	13.	WO 2005/001902	January 6, 2005	PCT	—	—		
	14.	WO 2004/114368	December 29, 2004	PCT	—	—		
	15.	WO 2005/015609	February 17, 2005	PCT	—	—		
	16.	WO 2003/033781	April 24, 2003	PCT	—	—		
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RSP	39.	T G. Kresse and J. Hafner, "Ab initio molecular dynamics for liquid metals", Phys. Rev. B47(1), pp. R558-561 (1993).
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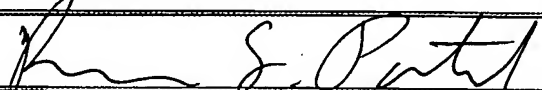
RSP	49.	E. A. V. Ebsworth, D. J. Hutchison, D. W. H. Rankin, "The Preparation, properties, and Gas-Phase Molecular-Structure of 1,1- Difluoro-2,2-Digermylbiphosphone", J. Chem. Res., Synop, 12, pp. 393, (1980).
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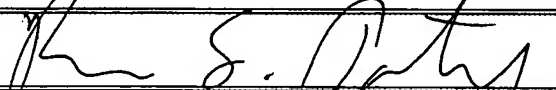
RSP ↓ ✓	59.	G. Davidson, L. A. Woodward, E. A. V. Ebsworth, G. M. Sheldrick, "The vibrational spectra and structure of trisilylarsine and trisilylstibine", Spectrochim. Acta, Part A, Vol: 23, pp. 2609-2616, (1967).
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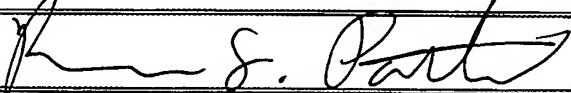
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RJP	91.	Mao R. W., et al., "Fabrication of 1.55 μ m Si-Based Resonant Cavity Enhanced Photodetectors Using Sol-Gel Bonding" IEEE Photonics Technology Letters 16(8), pp. 1930-1932 (2004).
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FORM PTO-1449 (Rev. 2-32)	U.S. Department of Commerce Patent and Trademark Office	Atty. Docket No.	Serial No.
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		05-720-US2	10/559,981
		Applicant:	
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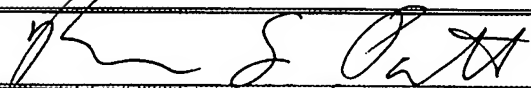
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COMMONLY OWNED CO-PENDING APPLICATIONS

Examiner Initial		
RJP	1.	Kouvetakis, et al., U.S. Patent Application No. 10/559,980, Filed on December 8, 2005.
RJP	2.	Kouvetakis, et al., U.S. Patent Application No. 10/559,979, Filed on December 8, 2005.

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